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12V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D T _A = +25°C
	$10m\Omega$ @ $V_{GS} = 4.5V$	9.3A
	12mΩ @ V_{GS} = 2.5 V	8.5A
12V	14mΩ @ V_{GS} = 1.8 V	7.9A
	18mΩ @ V _{GS} = 1.5V	6.9A
	41mΩ @ V _{GS} = 1.2V	4.6A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- DC-DC Converters
- Power Management Functions

Features

- Low On-Resistance
- · ESD Protected Gate
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

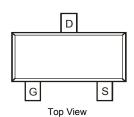
- Case: SC59
- Case Material Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.014 grams (approximate)



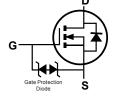


SC59





Pin Configuration



Equivalent Circuit

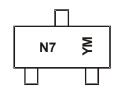
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1019USN-7	SC59	3,000/Tape & Reel
DMN1019USN-13	SC59	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N7 = Product Type Marking Code YM = Date Code Marking Y = Year ex: A = 2013 M = Month ex: 9 = September

Date Code Key

Year	2013	2014	2015	2016	2017	2018	2019	2020
Code	Α	В	С	D	Е	F	G	Н

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V_{DSS}	12	V
Gate-Source Voltage	V_{GSS}	±8	V		
Continuous Drain Current (Note 6) V - 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	9.3 7.4	А
Continuous Drain Current (Note 6) V _{GS} = 4.5V	t<10s	T _A = +25°C T _A = +70°C	ID	11 8.8	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	70	Α		
Maximum Body Diode Forward Current (Note 6)	Is	2	Α		

Thermal Characteristics

Characteristic	_	Symbol	Value	Units
Total Bower Dissipation (Note 5)	T _A = +25°C	D-	0.68	W
Total Power Dissipation (Note 5)	T _A = +70°C	P_{D}	0.4	VV
Thermal Decistance Junction to Ambient (Note 5)	Steady state	ReJA	160	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	RθJA	115	°C/W
Total Dower Dissination (Note 6)	T _A = +25°C	_	1.2	W
Total Power Dissipation (Note 6)	T _A = +70°C	P_{D}	0.83	VV
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	Б	96	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	68	°C/W
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	18	°C/W	
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

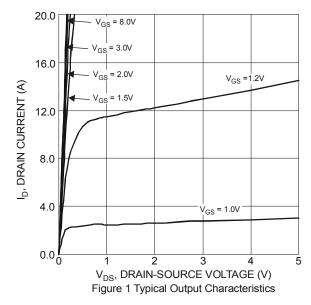
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

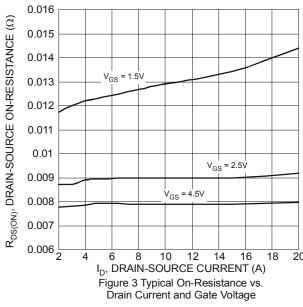
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	,		. 76			1000 50000000
Drain-Source Breakdown Voltage	BV _{DSS}	12	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} =12V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}			±2	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.35	0.53	8.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
			7	10		$V_{GS} = 4.5V, I_D = 9.7A$
			8	12		$V_{GS} = 2.5V, I_D = 9A$
Static Drain-Source On-Resistance	R _{DS(ON)}		10	14	mΩ	$V_{GS} = 1.8V, I_D = 8.1A$
	-	_	14	18		$V_{GS} = 1.5V, I_D = 4.5A$
			28	41		$V_{GS} = 1.2V, I_D = 2.4A$
Forward Transfer Admittance	IY _{fs} I	_	28	_	S	$V_{DS} = 4V, I_{D} = 9.7A$
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_S = 10A$
DYNAMIC CHARACTERISTICS (Note 8)	•			•		
Input Capacitance	C _{iss}	-	2426	_	pF	V 40V V 0V
Output Capacitance	Coss		396	_	pF	V _{DS} = 10V, V _{GS} = 0V, - f = 1MHz
Reverse Transfer Capacitance	C _{rss}		375	_	pF	1 - 11/1112
Gate Resistance	R_g		1.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 8V)	Qg		50.6	_		
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	27.3	_	nC	\\ - 4\\ \ \ - 104
Gate-Source Charge	Q _{gs}	-	3.4	_	IIC	$V_{DS} = 4V$, $I_D = 10A$
Gate-Drain Charge	Q_{gd}	_	5.2	_		
Turn-On Delay Time	t _{D(ON)}	-	7.6	_	ns	
Turn-Off Delay Time	t _{D(OFF)}		22.2	_	ns	V _{DD} = 4V, V _{GEN} = 5V, I _D = 10A,
Turn-On Rise Time	t _r		57.6	_	ns	$R_G = 1\Omega$, $R_L = 0.4\Omega$
Turn-Off Fall Time	t _f		16.8	_	ns	

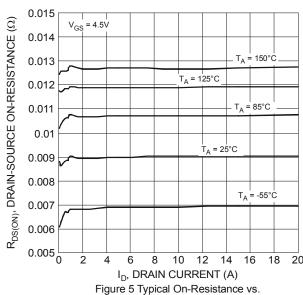
Notes:

- 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided. The power dissipation P_D is based on t<10s R_{BJA}.
 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2 oz. Copper, single sided. The power dissipation P_D is based on t<10s R_{BJA}.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to production testing.

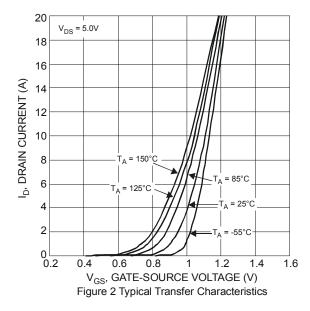


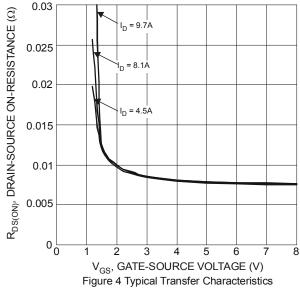






Drain Current and Temperature





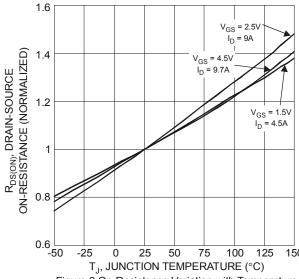
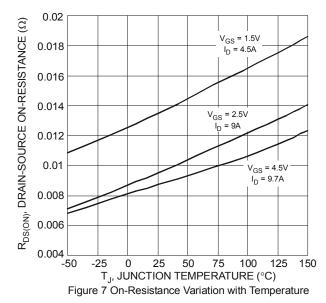
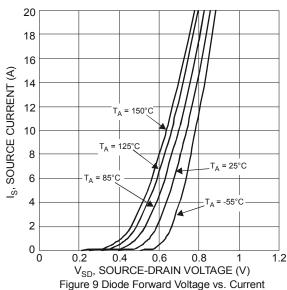
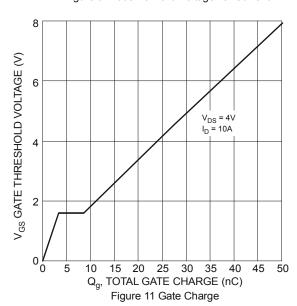


Figure 6 On-Resistance Variation with Temperature









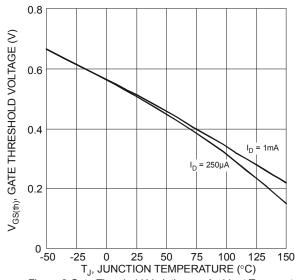
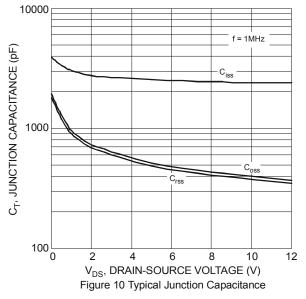
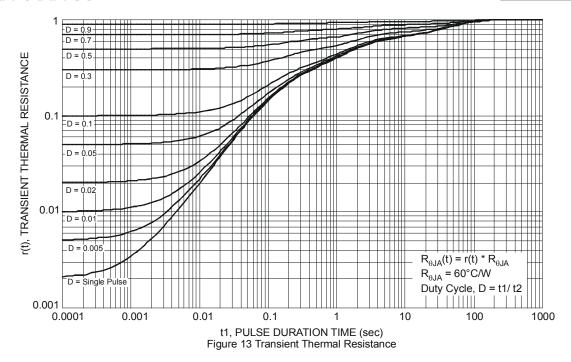


Figure 8 Gate Threshold Variation vs. Ambient Temperature



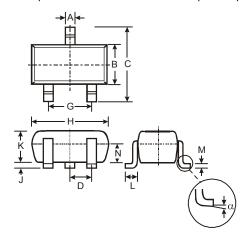
100
R_{DS(on)}
10
R_{DS}





Package Outline Dimensions

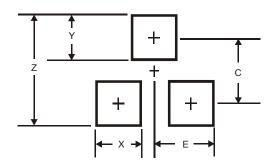
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SC59								
Dim	Min	Max	Тур						
Α	0.35	0.50	0.38						
В	1.50	1.70	1.60						
С	2.70	3.00	2.80						
D	-	-	0.95						
G	-	ı	1.90						
Н	2.90	3.10	3.00						
J	0.013	0.10	0.05						
K	1.00	1.30	1.10						
L	0.35	0.55	0.40						
M	0.10	0.20	0.15						
N	0.70	0.80	0.75						
α	0°	8°	-						
All	Dimens	ions in	mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.4
Х	0.8
Υ	1.0
С	2.4
E	1.35



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